

# ABSTRACT

A method of reflective lithography includes placing an adjustable (configurable) multi-faceted mirror in a condenser that collects and redirects light from a source to a reticle, an imaging system, and finally a target to be patterned. The adjustable multi-faceted mirror has a plurality of separately adjustable mirror elements or facets. The orientation of the mirror elements may be adjusted to adjust the characteristics of the light reaching a reflective reticle in order to achieve certain imaging characteristics at the resist layer that is being exposed. For example, coherence, shape of the illumination at the pupil of the imaging system, and/or configuration of the light output may be changed. The method and a corresponding system may be employed in extreme ultraviolet light (EUVL) lithography.